

21. (Original) The method in claim 20, wherein said sidewalls are perpendicular to a surface of said photodiode that receives incident light.
22. (Original) The method in claim 20, wherein said forming of said light sensing sidewalls comprises doping sidewalls of said trench to form a junction region between said sidewalls and said core that causes electron transfer when said sensing sidewalls are struck with light.
23. (Original) The method in claim 20, wherein said logic circuitry blocks light from said core.
24. (Original) The method in claim 20, wherein said forming of said trenches forms four vertical sidewalls around said core.
25. (Original) The method in claim 20, further comprising doping said core with impurities to form an n+ core and doping said sidewalls with impurities to form p+ sidewalls.
26. (Original) A method of forming an array of island photodiodes comprising:
forming cores in a substrate;
forming trenches in said substrate adjacent said cores;
forming light sensing sidewalls along said trenches; and
forming logic circuitry above each of said cores.

27. The method in claim 26, wherein said sidewalls are perpendicular to a surface of said photodiode that receives incident light.

28. (Original) The method in claim 26, wherein said forming of said light sensing sidewalls comprises doping sidewalls of said trench to form a junction region between said sidewalls and said cores that causes electron transfer when said sensing sidewalls are struck with light.

29. (Original) The method in claim 26, wherein said logic circuitry blocks light from said cores.

30. (Original) The method in claim 26, wherein said forming of said trenches forms four vertical sidewalls around each of said cores.

31. (Original) The method in claim 26, further comprising doping said cores with impurities to form an n⁺ core and doping said sidewalls with impurities to form p⁺ sidewalls.